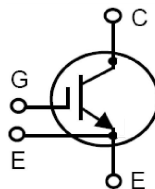


GenX3™ 300V IGBT

IXGN400N30A3

Ultra-Low-V_{sat} PT IGBT for
up to 10kHz Switching

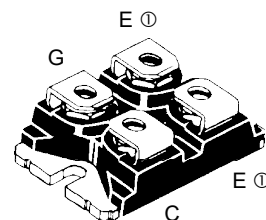


$$\begin{aligned} V_{CES} &= 300V \\ I_{C25} &= 400A \\ V_{CE(sat)} &\leq 1.15V \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	300	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	300	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	400	A
I_{C110}	$T_C = 110^\circ\text{C}$	200	A
I_{LRMS}	Terminal Current Limit	200	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	1200	A
SSOA	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 1\Omega$	$I_{CM} = 400$	A
(RBSOA)	Clamped Inductive Load	@ $0.8 \cdot V_{CES}$	V
P_C	$T_C = 25^\circ\text{C}$	735	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60Hz $t = 1\text{min}$ $I_{ISOL} \leq 1\text{mA}$ $t = 1\text{s}$	2500 3000	V~ V~
M_d	Mounting Torque Terminal Connection Torque (M4)	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter

① Either Emitter Terminal Can Be Used
as Main or Kelvin Emitter

Features

- Optimized for Low Conduction Losses
- High Current Capability
- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1\text{mA}, V_{GE} = 0V$	300		V
$V_{GE(th)}$	$I_C = 4\text{mA}, V_{CE} = V_{GE}$	3.0		5.5 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 2 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 400 nA
$V_{CE(sat)}$	$I_C = 100A, V_{GE} = 15V$, Note 1 $I_C = 400A$		1.70	1.15 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	100	170	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		19	nF
C_{oes}			1350	pF
C_{res}			190	pF
$Q_{g(on)}$	$I_C = 100\text{V}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		560	nC
Q_{ge}			83	C
Q_{gc}			185	nC
$t_{d(on)}$	Resistive Load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 1\Omega$		45	ns
t_r			45	ns
$t_{d(off)}$			210	ns
t_f			107	ns
$t_{d(on)}$	Resistive Load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 1\Omega$		47	ns
t_r			53	ns
$t_{d(off)}$			240	ns
t_f			315	ns
R_{thJC}				0.17 $^\circ\text{C/W}$
R_{thCK}		0.05		$^\circ\text{C/W}$

Note 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

Littelfuse reserves the right to change limits, test conditions, and dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

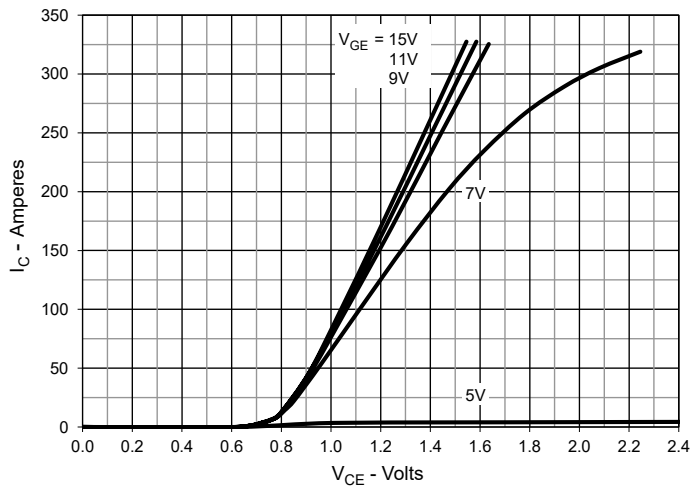
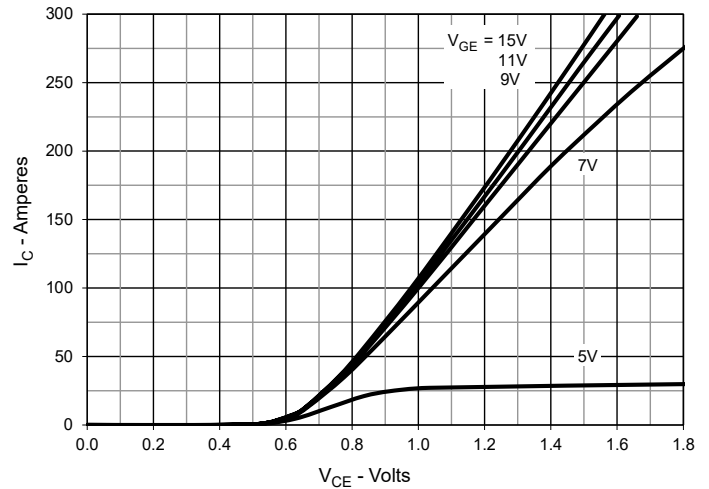
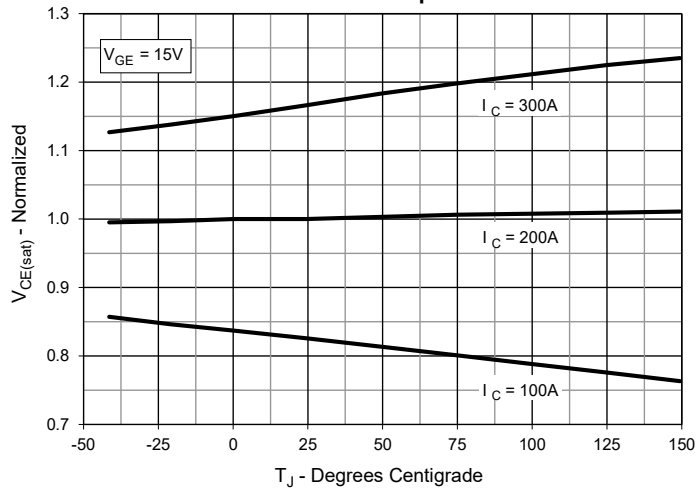
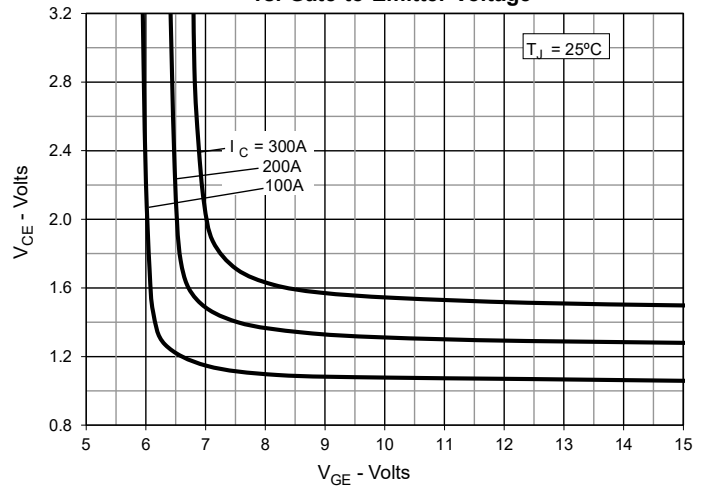
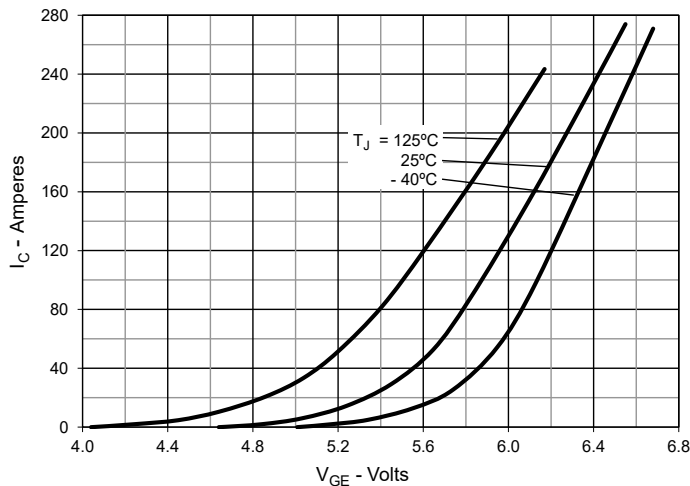
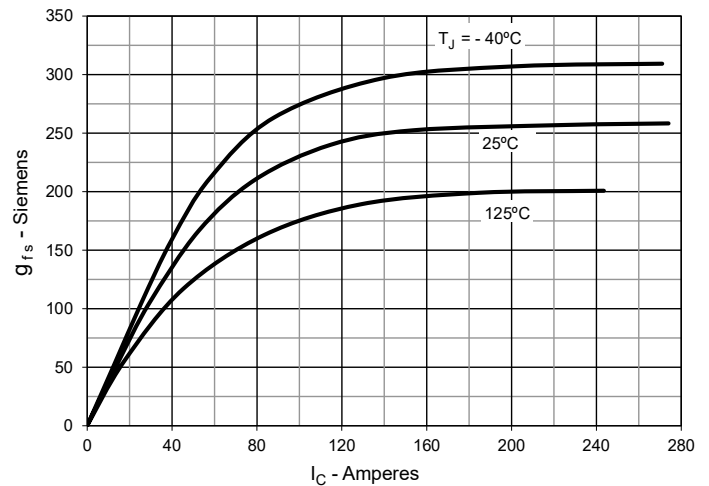
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 5. Input Admittance

Fig. 6. Transconductance


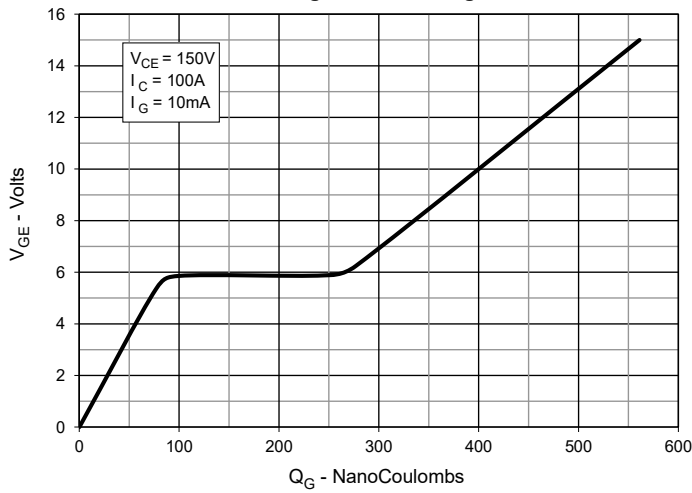
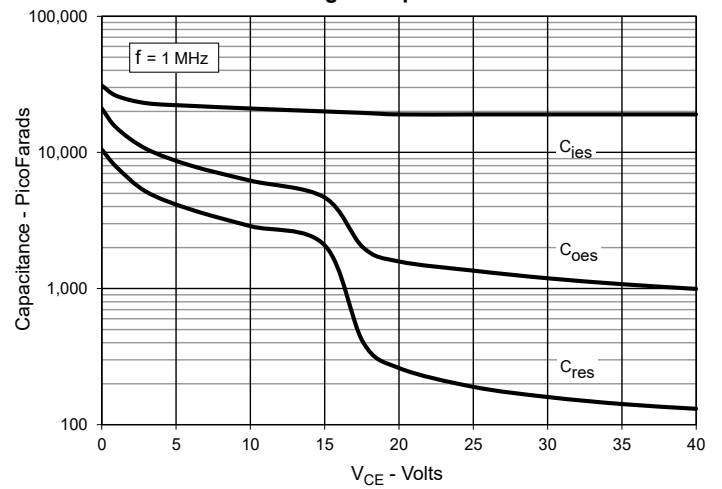
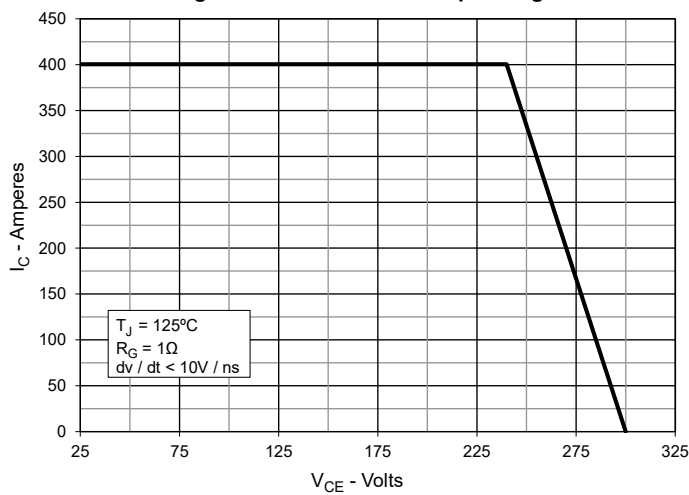
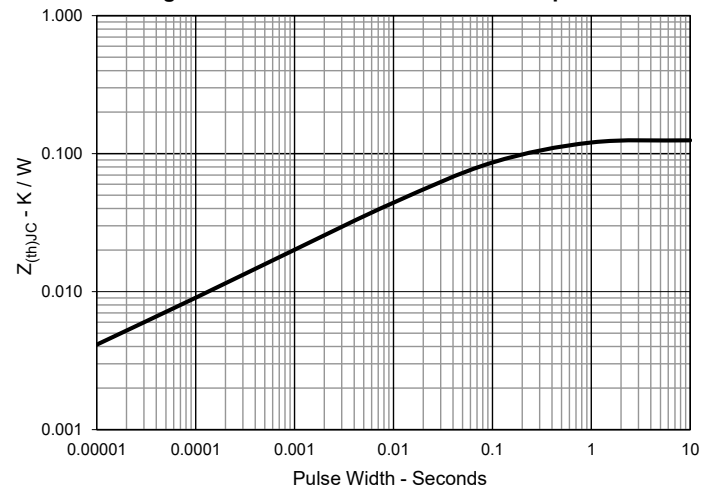
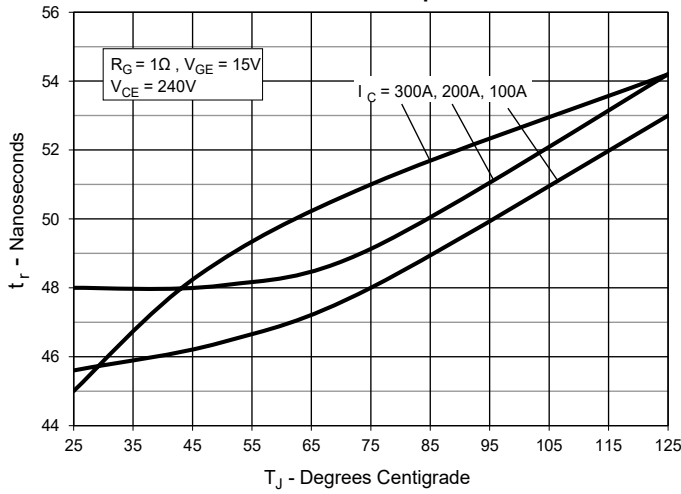
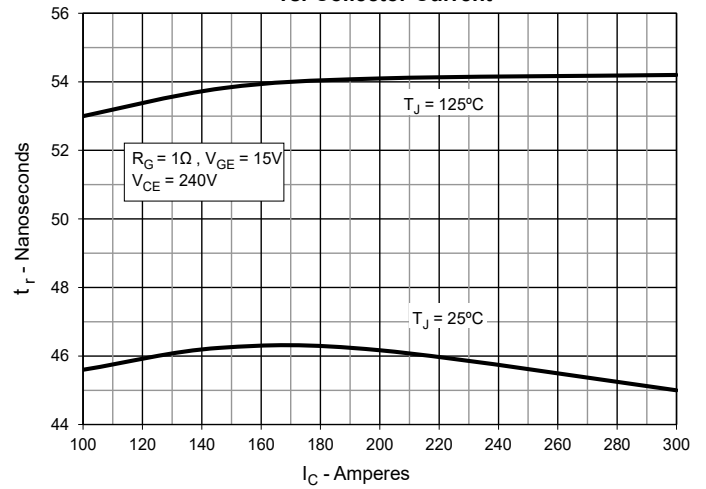
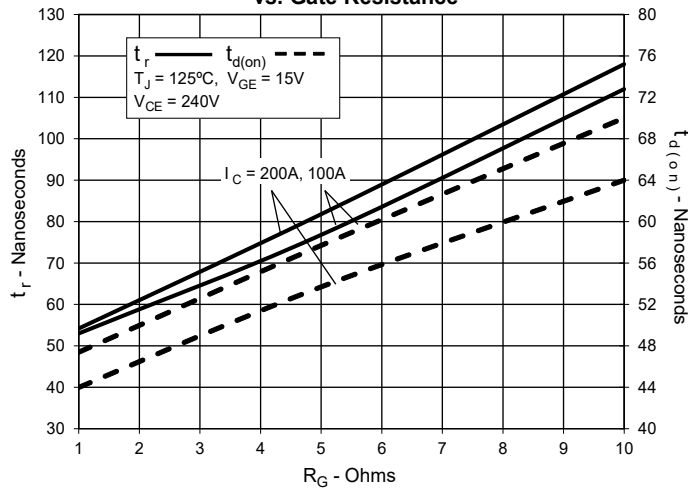
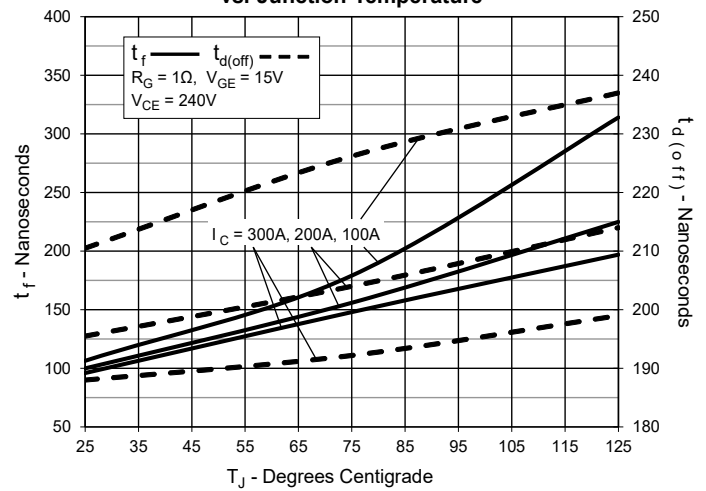
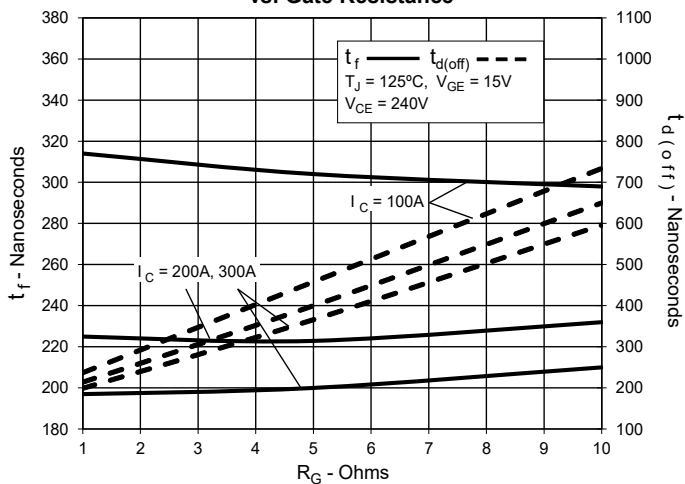
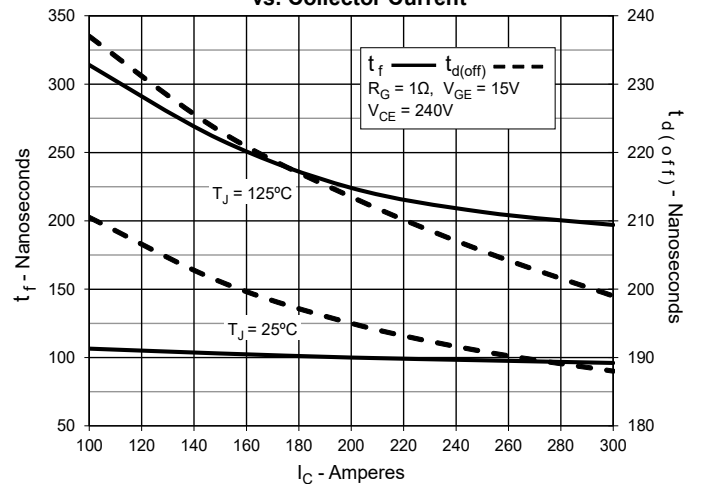
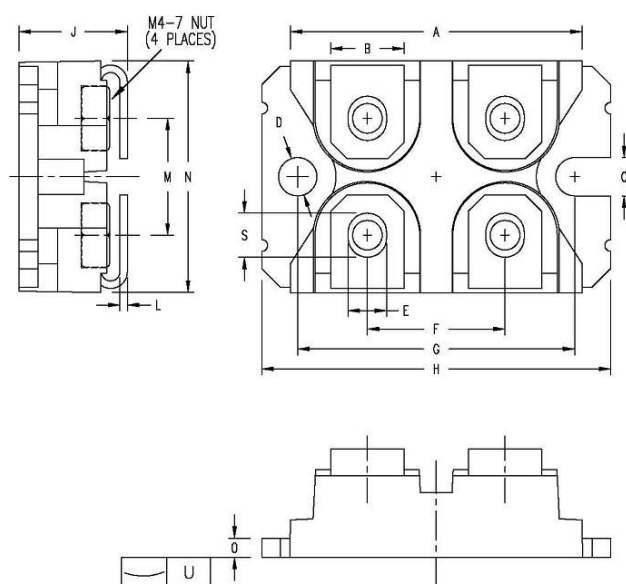
Fig. 7. Gate Charge

Fig. 8. Capacitance

Fig. 9. Reverse-Bias Safe Operating Area

Fig. 10. Maximum Transient Thermal Impedance


Fig. 11. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 12. Resistive Turn-on Rise Time vs. Collector Current

Fig. 13. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 14. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 15. Resistive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Collector Current


SOT-227 miniBLOC


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13